

Home Search Collections Journals About Contact us My IOPscience

Dependence of the Casimir–Polder interaction between an atom and a cavity wall on atomic and material properties

This article has been downloaded from IOPscience. Please scroll down to see the full text article. 2006 J. Phys. A: Math. Gen. 39 6583 (http://iopscience.iop.org/0305-4470/39/21/S57) View the table of contents for this issue, or go to the journal homepage for more

Download details: IP Address: 171.66.16.105 The article was downloaded on 03/06/2010 at 04:34

Please note that terms and conditions apply.

J. Phys. A: Math. Gen. 39 (2006) 6583-6587

doi:10.1088/0305-4470/39/21/S57

Dependence of the Casimir–Polder interaction between an atom and a cavity wall on atomic and material properties

V M Mostepanenko¹, J F Babb², A O Caride³, G L Klimchitskaya⁴ and S I Zanette³

¹ Noncommercial Partnership 'Scientific Instruments', Moscow, Russia

² Institute for Theoretical Atomic, Molecular and Optical Physics, Harvard-Smithsonian Center for Astrophysics, Cambridge, MA 02138, USA

³ Centro Brasileiro de Pesquisas Físicas, Rio de Janeiro, RJ 22290-180, Brazil

⁴ North-West Technical University, Millionnaya Street 5, St Petersburg, Russia

Received 28 October 2005, in final form 24 November 2005 Published 10 May 2006 Online at stacks.iop.org/JPhysA/39/6583

Abstract

The Casimir–Polder and van der Waals interactions between an atom and a flat cavity wall are investigated under the influence of real conditions including the dynamic polarizability of the atom, actual conductivity of the wall material and nonzero temperature of the wall. The cases of different atoms near metal and dielectric walls are considered. It is shown that to obtain accurate results for the atom–wall interaction at short separations, one should use the complete tabulated optical data for the complex refractive index of the wall material and the accurate dynamic polarizability of an atom. At relatively large separations in the case of a metal wall, one may use the plasma model dielectric function to describe the dielectric properties of the wall material. The obtained results are important for the theoretical interpretation of experiments on quantum reflection and Bose–Einstein condensation.

PACS numbers: 34.50.Dy, 12.20.Ds, 34.20.Cf

Recently, the study of dispersion interactions between an atom and a wall has assumed a new significance in connection with Bose–Einstein condensates of ultracold atoms [1–3]. The van der Waals and Casimir–Polder forces acting between dilute individual atoms, confined in a magnetic trap, and a wall may influence the stability of a condensate and the effective size of the trap [3]. As was shown in [4], the study of the collective oscillations of the Bose–Einstein condensate can provide a sensitive test of dispersion forces. This prediction was later supported both theoretically [5] and experimentally [6]. Dispersion interaction between an atom and a wall is also taken into account in quantum reflection of cold atoms on a

surface [7] and in dynamical interaction effects of fast atoms and molecules with solid surfaces [8]. Currently, the new asymptotic behaviour of the surface–atom interaction out of thermal equilibrium has been advanced [9]. Below we use the generic name 'Casimir–Polder' for all atom–wall interactions of a dispersive nature because the pure nonretarded regime occurs at separations from zero to a few nanometres only.

The theoretical basis for the description of the Casimir–Polder interaction between an atom at a separation a and a flat wall at temperature T in thermal equilibrium is given by the Lifshitz-type formula for the free energy [10–12]

$$\mathcal{F}(a,T) = -\frac{k_{\rm B}T}{8a^3} \left\{ 2\alpha(0) f(0) + \sum_{l=1}^{\infty} \alpha(i\zeta_l \omega_{\rm c}) \int_{\zeta_l}^{\infty} dy \, \mathrm{e}^{-y} \Big[(2y^2 - \zeta_l^2) r_{\parallel}(\zeta_l, y) + \zeta_l^2 r_{\perp}(\zeta_l, y) \Big] \right\}.$$
(1)

Here $\alpha(\omega)$ is the atomic dynamic polarizability, $k_{\rm B}$ is the Boltzmann constant, $\zeta_l = 4\pi l k_{\rm B} T a / (\hbar c)$ are the dimensionless Matsubara frequencies, $\omega_{\rm c} = c / (2a)$ is the characteristic frequency of the Casimir–Polder interaction, and the reflection coefficients for two independent polarizations of an electromagnetic field are defined as

$$r_{\parallel}(\zeta_l, y) = \frac{\varepsilon_l y - \sqrt{y^2 + \zeta_l^2(\varepsilon_l - 1)}}{\varepsilon_l y + \sqrt{y^2 + \zeta_l^2(\varepsilon_l - 1)}}, \qquad r_{\perp}(\zeta_l, y) = \frac{\sqrt{y^2 + \zeta_l^2(\varepsilon_l - 1)} - y}{\sqrt{y^2 + \zeta_l^2(\varepsilon_l - 1)} + y}, \tag{2}$$

where $\varepsilon_l \equiv \varepsilon(i\zeta_l\omega_c)$ is the permittivity of the wall material computed at imaginary Matsubara frequencies. For dielectrics $f(0) = [\varepsilon(0) - 1]/[\varepsilon(0) + 1]$ and for metals f(0) = 1.

In most calculations of the atom–wall interaction previously performed only the limiting cases of large and short separations were considered. The polarizability of the atom was taken into account in the static approximation [13] or in the framework of the single-oscillator model [14], and the dielectric properties of the wall material were oversimplified (e.g., by considering a metal wall to be made of ideal metal). The present experimental situation requires precise (1% accuracy) computations of the Casimir–Polder interaction in a wide separation range from about 3 nm (where the Lifshitz formula becomes applicable) to 10 μ m. In this paper, we present the results of such computations clarifying the atomic and material properties which are essential to attain the required accuracy.

We have performed numerical computations of the free energy (1), (2) for metastable He^{*}, Na and Cs atoms in the ground state located near the metal (Au), semiconductor (Si) and dielectric (SiO₂) walls at T = 300 K. (The modification on account of walls in the spontaneous emission of Rydberg atoms, obtained, e.g., by means of two lasers, is discussed in [15, 16]. However, thermal quanta at T = 300 K are too small to excite an atom from the ground state to some other states.) Three different descriptions for the dielectric properties of a metal were used: (i) as an ideal metal, (ii) using the dielectric permittivity from the free-electron plasma model $\varepsilon(i\xi) = 1 + \omega_p^2/\xi^2$ (where ω_p is the plasma frequency) and (iii) with $\varepsilon(i\xi)$ obtained by means of a dispersion relation using the tabulated optical data for the complex index of refraction [17]. The dielectric permittivity of a semiconductor or dielectric was described either by their static permittivity $\varepsilon(0)$ or by means of their tabulated optical data and the dispersion relation. The polarizability of an atom was represented by its static value $\alpha(0)$ or by means of the highly accurate *N*-oscillator model [18]

$$\alpha(i\zeta_{l}\omega_{c}) = \frac{e^{2}}{m} \sum_{n=1}^{N} \frac{f_{0n}}{\omega_{0n}^{2} + \omega_{c}^{2}\zeta_{l}^{2}},$$
(3)

Table 1. Free energy \mathcal{F} (in J) of the Casimir–Polder interaction between a He^{*} atom and Au and SiO₂ walls (columns (a)) and correction factors to it at different separations *a*. In columns labelled (a) the material of the wall and the atom are described by the optical tabulated data and accurate dynamic polarizability, respectively. In columns labelled (b) the metal is an ideal one and the dielectric permittivity of SiO₂ is static; the dynamic polarizability of the atom is the accurate one. In columns labelled (c) the wall materials are described by the tabulated optical data, and the dynamic polarizability of the atom is given by the single-oscillator model. In column (d) the metal is described by the plasma model and the dynamic polarizability of the atom is accurate.

<i>a</i> (nm)	He* near an Au wall				He* near a SiO ₂ wall		
	(a)	(b)	(c)	(d)	(a)	(b)	(c)
3	3.80×10^{-23}	1.16	0.956	0.937	1.61×10^{-23}	1.78	0.949
10	$9.95 imes 10^{-25}$	1.14	0.961	0.948	$4.18 imes 10^{-25}$	1.73	0.958
20	1.18×10^{-25}	1.14	0.973	0.959	4.94×10^{-26}	1.68	0.967
50	6.62×10^{-27}	1.13	0.984	0.976	2.71×10^{-27}	1.64	0.983
100	6.98×10^{-28}	1.11	0.991	0.981	2.76×10^{-28}	1.60	0.993
150	1.77×10^{-28}	1.10	0.997	0.992	6.93×10^{-29}	1.57	0.994

where m and e are the electron mass and charge, f_{0n} and ω_{0n} are the oscillator strength and frequency of the *n*th excited-state to ground-state transition, respectively. A more simplified single-oscillator model (equation (3) with N = 1) was also used. Computations show that at short separations (from 3 nm to about 150 nm), it is necessary to use the complete tabulated optical data for the complex index of refraction in order to find the most accurate results. For the dynamic polarizability of an atom, at shortest separations the highly accurate data for it should be used. With increasing atom-wall distance up to several tens of nanometres the single-oscillator model becomes applicable. These calculations are illustrated in table 1 by the example of a metastable He* atom near Au and SiO₂ walls (the analogous results for Na and Cs atoms near Au, Si and SiO_2 walls can be found in [11, 12]). The tabulated optical data for Au and SiO₂ were taken from [19], and the values of Au plasma frequency and SiO₂ static permittivity are $\omega_p = 9.0 \text{ eV} = 1.37 \times 10^{16} \text{ rad s}^{-1}$ and $\varepsilon(0) = 3.84$. The accurate data for the dynamic polarizability of metastable He^{*} (with a relative error of order 10^{-6}) were taken from [20] and the parameters of a single-oscillator model from [21] were used. As seen in table 1, the use of the ideal metal or the static dielectric permittivity approximations leads to errors up to 16% for metal and 78% for dielectric. These errors slowly decrease with increasing separation between the atom and the wall. The plasma model is a better approximation than the ideal metal approximation. It results in errors of about 5% at the shortest separations and becomes sufficiently exact when the separation approaches 150 nm. The use of the static atomic polarizability would result in much greater errors and for this reason it is omitted from table 1. At large separations, from 150 nm to a few micrometres, the effects of the atomic dynamic polarizability play a more important role than the effects of the finite conductivity of the metal. The single-oscillator model, however, is sufficient to achieve the required accuracy. The dielectric properties of a metal can be approximated by the plasma model. For dielectrics and semiconductors both tabulated optical data and the Ninham-Parsegian representation for the dielectric permittivity [22] are suitable for obtaining accurate results. For sufficiently large separations one can use the static dielectric permittivity of the wall. We illustrate these features using the example of a He^{*} atom near an Au wall. Due to the strongly nonmonotonic dependence of the free energy on separation, we plot along the vertical axis the ratio of the free energy to the Casimir–Polder energy $E(a) = -3\hbar c\alpha(0)/(8\pi a^4)$ of an atom near a wall made of ideal metal at T = 0. As is seen from figure 1, at separations $a > (4 - 5) \mu m$ all approaches lead to approximately equal values of the free energy.

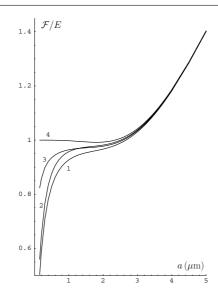


Figure 1. Normalized Casimir–Polder free energy for a metastable He^{*} atom near an Au wall versus separation. Lines 1, 2 take into account the dynamic polarizability of an atom (in the single-oscillator model) and describe the metal by the plasma model or as an ideal one, respectively. Lines 3, 4 describe the atom by the static polarizability and metal in analogy with lines 1, 2.

To conclude, results such as those presented in the columns labelled (a) in table 1 and by line 1 in figure 1 can be used in the interpretation of precision experiments on atom–surface interactions.

Acknowledgments

ITAMP is supported in part by a grant from the NSF to the Smithsonian Institution and Harvard University. VMM and GLK were partially supported by FAPERJ (process numbers E-26/170.132 and 170.409/2004) and by the Russian Foundation for Basic Research (grant no. 05-08-18119a).

References

- [1] Harber D M, McGuirk J M, Obrecht J M and Cornell E A 2003 J. Low Temp. Phys. 133 229
- [2] Leanhardt A E, Shin Y, Chikkatur A P, Kielpinski D, Ketterle W and Pritchard D E 2003 Phys. Rev. Lett. 90 100404
- [3] Lin Y, Teper I, Chin C and Vuletić V 2004 Phys. Rev. Lett. 92 050404
- [4] Antezza M, Pitaevskii L P and Stringari S 2004 Phys. Rev. A 70 053619
- [5] Carusotto I, Pitaevskii L P, Stringari S, Modugno G and Inguscio M 2005 Phys. Rev. Lett. 95 093202
- [6] Harber D M, Obrecht J M, McGuirk J M and Cornell E A 2005 Phys. Rev. A 72 033610
- [7] Oberst H, Tashiro Y, Shimizu K and Shimizu F 2005 Phys. Rev. A 71 052901
- [8] Villó-Pérez I, Abril I, Garcia-Molina R and Arista N R 2005 Phys. Rev. A 71 052902
- [9] Antezza M, Pitaevskii L P and Stringari S 2005 Phys. Rev. Lett. 95 113202
- [10] Lifshitz E M and Pitaevskii L P 1980 Statistical Physics Part II (Oxford: Pergamon)
- [11] Babb J F, Klimchitskaya G L and Mostepanenko V M 2004 Phys. Rev. A 70 042901
- [12] Caride A O, Klimchitskaya G L, Mostepanenko V M and Zanette S I 2005 Phys. Rev. A 71 042901
- [13] Casimir H B G and Polder D 1948 Phys. Rev. 73 360
- [14] Boström M and Sernelius B E 2000 Phys. Rev. A 61 052703

- [15] Hinds E A, Lai K S and Schnell M 1997 Phil. Trans. R. Soc. Lond. A 355 2353
- [16] Wu S-T and Eberlein C 2000 Proc. R. Soc. Lond. A 456 1931
- [17] Bordag M, Mohideen U and Mostepanenko V M 2001 Phys. Rep. 353 1
- [18] Shih A and Parsegian V A 1975 Phys. Rev. A 12 835
- [19] Palik E D (ed) 1985 Handbook of Optical Constants of Solids (New York: Academic)
- [20] Yan Z-C and Babb J F 1998 Phys. Rev. A 58 1247
- [21] Brühl R, Fouquet P, Grisenti R E, Toennies J P, Hegerfeldt G C, Köhler T, Stoll M and Walter C 2002 Europhys. Lett. 59 357
- [22] Mahanty J and Ninham B W 1976 Dispersion Forces (New York: Academic)